

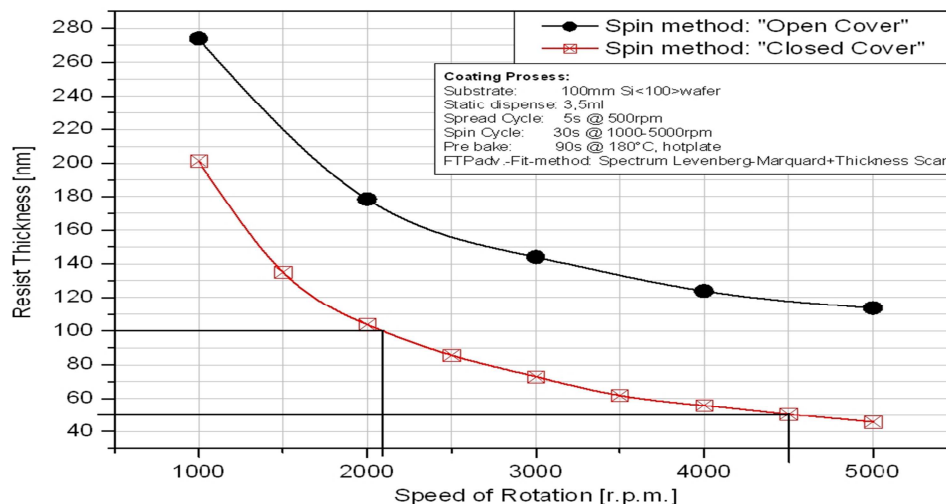
Process data for e-beam resist AR-P 672.03 (PMMA 950K)

Resist used:

Supplier: Allresist GmbH (www.Allresist.de)
Name / Order Code: AR-P 672.03
Solid Content / Solvent: 3% / Anisole
Type: High-resolution positive tone e-beam resist

Coating:

Substrate: Silicon <100>
Dehydration: 90s@180°C on hotplate
Adhesion: no Adhesion promoter needed
Pre bake: 90s@180°C on hotplate
RPM / Film thickness: see spin curve



Exposure:

Film Thickness: 100nm
Parameters: Aperture: 30µm, WD: 10mm WF: 100µm
Dose (EHT: 10kV): Area: 70µC/cm², Line: 210pC/cm, Dot: 0,005pC
Dose (EHT: 50kV): Area: 350µC/cm²
Pattern: Demo.csf
Post Exposure Bake: no PEB needed
Developer: IPA+MIBK (3:1) + 2% H₂O
Developing time: 30sec (22°C)
Stopper: IPA
Stopping time: 30sec (22°C)
Dry: low nitrogen flow